Atty. Dkt. No. AMAT3577/DD/BCVD/JW

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re Application of:

Judy Huang

Serial No.: 09/336,525

Confirmation No.: 7748

Filed:

June 18, 1999

For:

Plasma Treatment to

Enhance Adhesion and to Minimize Oxidation of Carbon-Containing Layers Group Art Unit: 1762

Examiner:

M. Padgett

SEP 1 9 2001

Assistant Commissioner for Patents Washington, D.C. 20231

CERTIFICATE OF MAILING 37 CFR 1.8

I hereby certify that this correspondence is being deposited on September 12, 2001, with the United States Postal Service as First Class Mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231.

Dear Sir:

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9/12/01

Signature

## **RESPONSE TO OFFICE ACTION DATED JUNE 12, 2001**

In response to the Office Action dated June 12, 2001, having a shortened statutory period for response set to expire on September 12, 2001, please enter the following amendments and reconsider the claims pending in the application for reasons discussed below.

## IN THE SPECIFICATIONS:

Please replace the paragraph at pg. 6 lines 8 –19, with the following paragraph:

B

The process regimes yield a SiC material having a dielectric constant of less than 7, preferably about 5 or less, and most preferably about 4.2 or less. To deposit such a SiC layer on a 200 mm wafer, a reactive gas source such as trimethylsilane is flown into a reaction chamber, such as a CENTURA® DxZ<sup>TM</sup> chamber, without a substantial source of oxygen introduced into the reaction zone, the trimethylsilane flowing at a